Form PTO-1449 U.S. DEPARTMENT OF COMMERCE ATTY. DOCKET NO. SERIAL NO. PATENT AND TRADEMARK OFFICE M122-1694 09/885,393 OF ART CITED BY APPLICANT APPLICANT Micron Technology, Inc. (Use several sheets if necessary) GROUP FILING DATE June 19, 2001 U.S. PATENT DOCUMENTS Date Class Subclass Filing Date Document Name *Examiner Number If Appropriate Initial WAD 4,474,975 10/2/84 Clemons et al. AA ΑB 5,962,581 10/5/99 Hayase et al. 5,677,015 AC 10/14/97 Hasegawa 5,783,493 ΑD 7/21/98 Yeh et al. Lin et al. 5,807,660 9/15/98 ΑE ΑF 4,833,096 5/23/89 Huang et al. AG 5,405,489 4/11/95 Kim et al. ΑH 5,470,772 11/28/95 Woo ΑI 5,652,187 7/29/97 Kim et al. ΑJ 5,656,337 8/12/97 Park et al. FOREIGN PATENT DOCUMENTS Date Subclass Document Country Translation Number Yes EVID EPO ΑK 0 942330 9/99 NO 9 050993 2/97 ΑL Japan (UT) 9/94 AM 406244172 Japan 593,727 AN 10/47 GB OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, Etc.) ΑO Weidman, T. et al., "New Photodefinable Glass Etch Masks for Entirely Dry Photolithography: Plasma Deposited Organosilicon Hydride Polymers", Appl. Phys. Lett., Vol. 62, No. 4, Jan. 25, 1993, pp. 372-374. Weidman, T. et al., "All Dry Lithography: Applications of Plasma Polymerized Methylsilane as a Single Layer Resist and Silicon Dioxide Precursor", J. Photopolym. Sci. Technol., Vol. 8, No. 4, 1995, pp. 679-686. AQ Joubert, O. et al., "Application of Plasma Polymerized Methylsilane in an All Dry Resist Process for 193 and 248nm Lithography", Microelectronic Engineering 30 (1996), pp. 275-278. **EXAMINER** DATE CONSIDERED *EXAMINER: Initial if reference_considered,-whether-or-not-citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant. RECEIVE AUG 03 2001 TC 17C.5

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6	AP	/	McClatchie	, S. et a	al., "Low Dielec	etric Constant Flowfill* Technol	ogy for IMD Applicat	ions", Proce	ed. of	3d Inte	rnatl. Dielec	trics for
WID .			ULSI M	lultilevel	l Interconnectio	n Conf, Santa Clara, CA, Feb. 1	997, pp. 34-40.					
MAD	AQ	/	Beekman,	K. et a	I., "Sub-Micron	Gap Fill and In-Situ Planarisati	on Using Flowfill To	chnology",	ULSI (Conf, Po	ortland, OR,	
		-	Oct. 19	95, pp.	1-7.							
	AR	/	Kiermasz	A. et al.	. Planarisation	for Sub-Micron Devices Utilisin	g a New Chemistry".	DUMIC-Co	nf., Ca	liornia.	Feb. 1995	pp1-2.

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	AD	4,695,859	9/22/87	Guha et al.	_	_	—		
	AE	5,061,509	10/29/91	Naito et al.					
	AF	4,600,671	7/15/86	Saitoh et al.					
	AG	5,753,320	5/19/98	Mikoshiba et al.				-	
	AH	5,356,515	10/18/94	Tahara et al.					
	AI	6,054,379	4/25/00	Yau et al.					
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U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE

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		ВВ	6,198,144	3/2001	Pan et al.			257	412			
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		BD	5,994,730	11/1999	Shrivasta	va et al.		257	306		,	·
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Sheet 3 of 3 Form PTO-144 U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE ATTY. DOCKET NO. M122-1694 SERIAL NO. 09/885,393 LIST OF ART CITED BY APPLICANT APPLICANT (Use several sheets if necessary) Richard Holscher et al. FILING DATE GROUP June 19, 2001 U.S. PATENT DOCUMENTS *Examiner Document Date Initial Number Class ВО 6,060,766 5/2000 Mehta et al. 257 ВP 6,133,613 10/2000 Yao et al. 257 BQ BR BS вт BU ΒV BW ВX BY ΒZ FOREIGN PATENT DOCUMENTS Document Date Country Number Class Subclass Translation CA Yes No CB CC CD CE OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, Etc.) CF CG СН EXAMINER DATE CONSIDERED *EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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con .	АА	6,087,267	06/00	Dockrey et al.	438	719		
WTD.	AB	5,543,654	08/96	Dennen	257	386		
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(M)	AD	5,872,035	02/99	Kim et al.	438	261		
(CMD)	AE	4,444,617	04/84	Whitcomb	156	643		
WAD	AF	6,071,799	06/00	Park et al.	438	595		
(MD)	AG	5,691,212	11/97	Tsai et al.	437	24		
42	АН	6,187,657 B1	02/01	Xiang et al.	438	596		
KNO	ΑI	5,792,689	08/98	Yang et al.	438	253		
CNO	AJ	20010023051	Nub. Date 09/01	Rolfson et al. (P atent Application Publicatio n)	430	311		
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